

Advantech

AQD-D4U8GN21-SG

Datasheet

Rev. 1.0
2015-03-13

Description

DDR4 Unbuffered DIMM is high-speed, low power memory module that use 512Mx8bits DDR4 SDRAM in FBGA package and a 4Kbits serial EEPROM on a 288-pin printed circuit board. DDR4 Unbuffered DIMM is a Dual In-Line Memory Module and is intended for mounting into 288-pin edge connector sockets.

Synchronous design allows precise cycle control with the use of system clock. Data I/O transactions are possible on both edges of DQS. Range of operation frequencies, programmable latencies allow the same device to be useful for a variety of high bandwidth, high performance memory system applications.

Features

- RoHS compliant products.
- JEDEC standard 1.2V ± 0.06V power supply
- VDDQ=1.2V ± 0.06V
- Clock Freq: 1067MHZ for 2133Mb/s/Pin.
- Programmable CAS Latency: 10,11,12,13,14,15,16
- Programmable Additive Latency (Posted /CAS): 0,CL-2 or CL-1 clock
- Programmable /CAS Write Latency (CWL) = 11, 14(DDR4-2133)
- 8 bit pre-fetch
- Burst Length: 4, 8
- Bi-directional Differential Data-Strobe
- On Die Termination with ODT pin
- Serial presence detect with EEPROM
- On DIMM Thermal Sensor
- Asynchronous reset

Pin Identification

| Symbol | Function |
|---------------|--|
| A0~A17 | SDRAM address bus |
| BA0, BA1 | SDRAM bank select |
| BG0, BG1 | SDRAM bank group select |
| RAS_n | SDRAM row address strobe |
| CAS_n | SDRAM column address strobe |
| WE_n | SDRAM write enable |
| CS0_n, CS1_n | DIMM Rank Select Lines |
| CKE0, CKE1 | SDRAM clock enable lines |
| ODT0, ODT1 | SDRAM on-die termination control lines |
| ACT_n | SDRAM activate |
| DQ0~DQ63 | DIMM memory data bus |
| CB0~CB7 | DIMM ECC check bits |
| DQS0_t~DQS8_t | SDRAM data strobes (positive line of differential pair) |
| DQS0_c~DQS8_c | SDRAM data strobes (negative line of differential pair) |
| CK0_t, CK1_t | SDRAM clocks (positive line of differential pair) |
| CK0_c, CK1_c | SDRAM clocks (negative line of differential pair) |
| PARITY | SDRAM parity input |
| VDD | SDRAM I/O and core power supply |
| 12 V | Optional power Supply on socket but not used on UDIMM |
| VREFCA | SDRAM command/address reference supply |
| VSS | Power supply return (ground) |
| VDDSPD | Serial SPD EEPROM positive power supply |
| SCL | I ² C serial bus clock for EEPROM |
| SDA | I ² C serial bus data line for EEPROM |
| SA0~SA2 | I ² C slave address select for EEPROM |
| ALERT_n | SDRAM ALERT_n |
| VPP | SDRAM Supply |
| RESET_n | Set DRAMs to a Known State |
| EVENT_n | SPD signals a thermal event has occurred |
| VTT | SDRAM I/O termination supply |
| RFU | Reserved for future use |

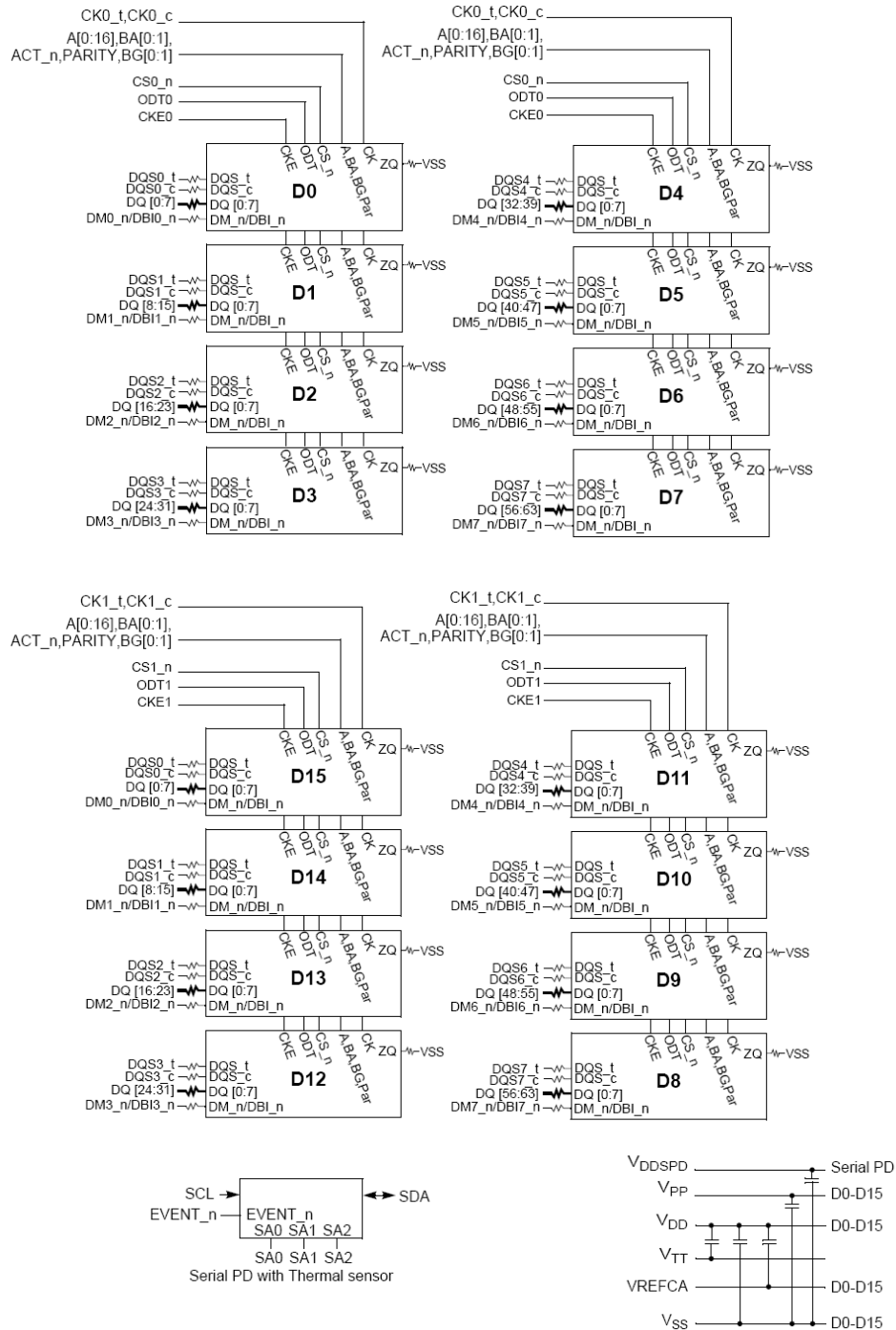
Pin Assignments

| Pin No | Pin Name | Pin No | Pin Name | Pin No | Pin Name | Pin No | Pin Name | Pin No | Pin Name | Pin No | Pin Name |
|--------|----------|--------|-----------|--------|----------|--------|----------|--------|----------|--------|----------|
| 01 | NC | 49 | NC | 97 | DQ32 | 145 | NC | 193 | VSS | 241 | VSS |
| 02 | VSS | 50 | VSS | 98 | VSS | 146 | VREFCA | 194 | NC | 242 | DQ33 |
| 03 | DQ4 | 51 | NC | 99 | NC | 147 | VSS | 195 | VSS | 243 | VSS |
| 04 | VSS | 52 | NC | 100 | NC | 148 | DQ5 | 196 | DQS8_c | 244 | DQS4_c |
| 05 | DQ0 | 53 | VSS | 101 | VSS | 149 | VSS | 197 | DQS8_t | 245 | DQS4_t |
| 06 | VSS | 54 | NC | 102 | DQ38 | 150 | DQ1 | 198 | VSS | 246 | VSS |
| 07 | NC | 55 | VSS | 103 | VSS | 151 | VSS | 199 | NC | 247 | DQ39 |
| 08 | NC | 56 | NC | 104 | DQ34 | 152 | DQS0_c | 200 | VSS | 248 | VSS |
| 09 | VSS | 57 | VSS | 105 | VSS | 153 | DQS0_t | 201 | NC | 249 | DQ35 |
| 10 | DQ6 | 58 | RESET_n | 106 | DQ44 | 154 | VSS | 202 | VSS | 250 | VSS |
| 11 | VSS | 59 | VDD | 107 | VSS | 155 | DQ7 | 203 | CKE1 | 251 | DQ45 |
| 12 | DQ2 | 60 | CKE0 | 108 | DQ40 | 156 | VSS | 204 | VDD | 252 | VSS |
| 13 | VSS | 61 | VDD | 109 | VSS | 157 | DQ3 | 205 | RFU | 253 | DQ41 |
| 14 | DQ12 | 62 | ACT_n | 110 | NC | 158 | VSS | 206 | VDD | 254 | VSS |
| 15 | VSS | 63 | BG0 | 111 | NC | 159 | DQ13 | 207 | BG1 | 255 | DQS5_c |
| 16 | DQ8 | 64 | VDD | 112 | VSS | 160 | VSS | 208 | ALERT_n | 256 | DQS5_t |
| 17 | VSS | 65 | A12/BC_n | 113 | DQ46 | 161 | DQ9 | 209 | VDD | 257 | VSS |
| 18 | NC | 66 | A9 | 114 | VSS | 162 | VSS | 210 | A11 | 258 | DQ47 |
| 19 | NC | 67 | VDD | 115 | DQ42 | 163 | DQS1_c | 211 | A7 | 259 | VSS |
| 20 | VSS | 68 | A8 | 116 | VSS | 164 | DQS1_t | 212 | VDD | 260 | DQ43 |
| 21 | DQ14 | 69 | A6 | 117 | DQ52 | 165 | VSS | 213 | A5 | 261 | VSS |
| 22 | VSS | 70 | VDD | 118 | VSS | 166 | DQ15 | 214 | A4 | 262 | DQ53 |
| 23 | DQ10 | 71 | A3 | 119 | DQ48 | 167 | VSS | 215 | VDD | 263 | VSS |
| 24 | VSS | 72 | A1 | 120 | VSS | 168 | DQ11 | 216 | A2 | 264 | DQ49 |
| 25 | DQ20 | 73 | VDD | 121 | NC | 169 | VSS | 217 | VDD | 265 | VSS |
| 26 | VSS | 74 | CK0_t | 122 | NC | 170 | DQ21 | 218 | CK1_t | 266 | DQS6_c |
| 27 | DQ16 | 75 | CK0_c | 123 | VSS | 171 | VSS | 219 | CK1_c | 267 | DQS6_t |
| 28 | VSS | 76 | VDD | 124 | DQ54 | 172 | DQ17 | 220 | VDD | 268 | VSS |
| 29 | NC | 77 | VTT | 125 | VSS | 173 | VSS | 221 | VTT | 269 | DQS5 |
| 30 | NC | 78 | EVENT_n | 126 | DQ50 | 174 | DQS2_c | 222 | PARITY | 270 | VSS |
| 31 | VSS | 79 | A0 | 127 | VSS | 175 | DQS2_t | 223 | VDD | 271 | DQ51 |
| 32 | DQ22 | 80 | VDD | 128 | DQ60 | 176 | VSS | 224 | BA1 | 272 | VSS |
| 33 | VSS | 81 | BA0 | 129 | VSS | 177 | DQ23 | 225 | A10/AP | 273 | DQ61 |
| 34 | DQ18 | 82 | RAS_n/A16 | 130 | DQ56 | 178 | VSS | 226 | VDD | 274 | VSS |
| 35 | VSS | 83 | VDD | 131 | VSS | 179 | DQ19 | 227 | RFU | 275 | DQ57 |
| 36 | DQ28 | 84 | CS0_n | 132 | NC | 180 | VSS | 228 | WE_n/A14 | 276 | VSS |
| 37 | VSS | 85 | VDD | 133 | NC | 181 | DQ29 | 229 | VDD | 277 | DQS7_c |
| 38 | DQ24 | 86 | CAS_n/A15 | 134 | VSS | 182 | VSS | 230 | NC | 278 | DQS7_t |
| 39 | VSS | 87 | ODT0 | 135 | DQ62 | 183 | DQ25 | 231 | VDD | 279 | VSS |
| 40 | NC | 88 | VDD | 136 | VSS | 184 | VSS | 232 | A13 | 280 | DQ63 |
| 41 | NC | 89 | CS1_n | 137 | DQ58 | 185 | DQS3_c | 233 | VDD | 281 | VSS |
| 42 | VSS | 90 | VDD | 138 | VSS | 186 | DQS3_t | 234 | NC | 282 | DQ59 |
| 43 | DQ30 | 91 | ODT1 | 139 | SA0 | 187 | VSS | 235 | NC | 283 | VSS |
| 44 | VSS | 92 | VDD | 140 | SA1 | 188 | DQ31 | 236 | VDD | 284 | VDDSPD |
| 45 | DQ26 | 93 | NC | 141 | SCL | 189 | VSS | 237 | NC | 285 | SDA |
| 46 | VSS | 94 | VSS | 142 | VPP | 190 | DQ27 | 238 | SA2 | 286 | VPP |
| 47 | NC | 95 | DQ36 | 143 | VPP | 191 | VSS | 239 | VSS | 287 | VPP |
| 48 | VSS | 96 | VSS | 144 | RFU | 192 | NC | 240 | DQ37 | 288 | VPP |

Note:

1. VPP is 2.5V DC.
2. Pin 230 is defined as NC for UDIMMs, RDIMMs and LRDIMMs. Pin 230 is defined as SAVE_n for NVDIMMs.
3. Pins 1 and 145 are defined as NC for UDIMMs, RDIMMs and LRDIMMs. Pins 1 and 145 are defined as 12V for Hybrid /NVDIMM
4. The 5th VPP is required on all modules, DIMMs.

Block Diagram 8GB, 1Gx64 Module(2 Rank x8)



This technical information is based on industry standard data and tests believed to be reliable. However, Transcend makes no warranties, either expressed or implied, as to its accuracy and assume no liability in connection with the use of this product. Transcend reserves the right to make changes in specifications at any time without prior notice.

Operating Temperature Condition

| Parameter | Symbol | Rating | Unit | Note |
|-----------------------|--------|---------|------|------|
| Operating Temperature | TOPER | 0 to 85 | °C | 1,2 |

Note: Operating Temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JESD51-2 standard.
At 0 - 85°C, operation temperature range are the temperature which all DRAM specification will be supported.

Absolute Maximum DC Ratings

| Parameter | Symbol | Value | Unit | Note |
|-------------------------------------|-----------|------------|------|------|
| Voltage on VDD relative to Vss | VDD | -0.3 ~ 1.5 | V | 1 |
| Voltage on VDDQ pin relative to Vss | VDDQ | -0.3 ~ 1.5 | V | 1 |
| Voltage on VPP pin relative to Vss | VPP | -0.3 ~ 3.0 | V | 3 |
| Voltage on any pin relative to Vss | VIN, VOUT | -0.3 ~ 1.5 | V | 1 |
| Storage temperature | TSTG | -55~+100 | °C | 1,2 |

Note: Stress greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
Storage Temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JESD51-2 standard.
VPP must be equal or greater than VDD/VDDQ at all times.

AC & DC Operating Conditions

Recommended DC operating conditions (SSTL –1.5)

| Parameter | Symbol | Rating | | | Unit | Notes |
|---------------------------|--------|--------|------|------|------|-------|
| | | Min | Typ. | Max | | |
| Supply voltage | VDD | 1.14 | 1.2 | 1.26 | V | 1, 2 |
| Supply voltage for Output | VDDQ | 1.14 | 1.2 | 1.26 | V | 1, 2 |
| Wordline supply voltage | VPP | 2.375 | 2.5 | 2.75 | V | 3 |

Note: Under all conditions VDDQ must be less than or equal to VDD.
VDDQ tracks with VDD, AC parameters are measured with VDD and VDDQ tied together.
DC bandwidth is limited to 20MHz

Single-ended AC & DC input levels for Command and Address

| Parameter | Symbol | DDR4-1600/1866/2133 | | Unit | Note |
|---------------------------------|------------|---------------------|------------|------|------|
| | | Min | Max | | |
| I/O Reference Voltage (CMD/ADD) | VREFCA(DC) | 0.49*VDDQ | 0.51*VDDQ | V | 1,2 |
| DC Input Logic High | VIH(DC) | VREF+0.075 | VDD | V | |
| DC Input Logic Low | VIL(DC) | VSS | VREF-0.075 | V | |
| AC Input Logic High | VIH(AC) | VREF+0.1 | Note 1 | V | |
| AC Input Logic Low | VIL(AC) | Note 1 | VREF-0.1 | V | |

Note: The AC peak noise on VREFCA may not allow VREFCA to deviate from VREFCA(DC) by more than $\pm 1\%$ VDD (for reference : approx. $\pm 12\text{mV}$)
For reference : approx. $VDD/2 \pm 12\text{mV}$

Differential AC and DC Input Levels

| Parameter | Symbol | DDR4-1600/1866/2133 | | Unit | Note |
|----------------------------|-------------|----------------------|----------------------|------|------|
| | | Min | Max | | |
| differential input high DC | VIHdiff(DC) | +0.150 | NOTE 3 | V | 1 |
| differential input low DC | VILdiff(DC) | NOTE 3 | -0.150 | V | 1 |
| differential input high AC | VIHdiff(AC) | 2 x (VIH(AC) - VREF) | NOTE 3 | V | 2 |
| differential input low AC | VILdiff(AC) | NOTE 3 | 2 x (VIL(AC) - VREF) | V | 2 |

Note: Used to define a differential signal slew-rate.
 for CK_t - CK_c use VIH.CA/VIL.CA(AC) of ADD/CMD and VREFCA;
 These values are not defined; however, the differential signals CK_t - CK_c, need to be within the respective limits (VIH.CA(DC) max, VIL.CA(DC)min) for single-ended signals as well as the limitations for overshoot and undershoot.

Single-ended AC & DC output levels

| Parameter | Symbol | DDR4-1600/1866/2133 | Unit | Note |
|----------------------------------|---------|---------------------|------|------|
| DC output high measurement level | VOH(DC) | 1.1 x VDDQ | V | |
| DC output mid measurement level | VOM(DC) | 0.8 x VDDQ | V | |
| DC output low measurement level | VOL(DC) | 0.5 x VDDQ | V | |
| AC output high measurement level | VOH(AC) | (0.7 + 0.15) x VDDQ | V | 1 |
| AC output low measurement level | VOL(AC) | (0.7 - 0.15) x VDDQ | V | 1 |

Note: The swing of $\pm 0.15 \times VDDQ$ is based on approximately 50% of the static single-ended output peak-to-peak swing with a driver impedance of $RZQ/7\Omega$ and an effective test load of 50Ω to $VTT = VDDQ$.

Differential AC & DC output levels

| Parameter | Symbol | DDR4-1600/1866/2133 | Unit | Note |
|---|-------------|---------------------|------|------|
| AC differential output high measurement level | VOHdiff(AC) | +0.3 x VDDQ | V | 1 |
| AC differential output low measurement level | VOLdiff(AC) | -0.3 x VDDQ | V | 1 |

Note: The swing of $\pm 0.3 \times VDDQ$ is based on approximately 50% of the static differential output peak-to-peak swing with a driver impedance of $RZQ/7\Omega$ and an effective test load of 50Ω to $VTT = VDDQ$ at each of the differential outputs.

IDD Specification parameters Definition

(IDD values are for full operating range of Voltage and Temperature)

8GB, 1Gx64 Module(2 Rank x8)

| Parameter | Symbol | DDR4 2133 CL15 | Unit |
|--|--------|----------------|------|
| Operating One bank Active-Precharge current; tCK = tCK(IDD), tRC = tRC(IDD), tRAS = tRASmin(IDD); CKE is HIGH, /CS is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING | IDD0 | TBD | mA |
| Operating One bank Active-read-Precharge current; IOU _T = 0mA; BL = 8, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRC = tRC(IDD), tRAS = tRASmin(IDD), tRCD = tRCD(IDD); CKE is HIGH, /CS is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W | IDD1 | TBD | mA |
| Precharge power-down current; All banks idle; tCK = tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING | IDD2P | TBD | mA |
| Precharge quiet standby current; All banks idle; tCK = tCK(IDD); CKE is HIGH, /CS is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING | IDD2Q | TBD | mA |
| Precharge standby current; All banks idle; tCK = tCK(IDD); CKE is HIGH, /CS is HIGH; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING | IDD2N | TBD | mA |
| Active power - down current; All banks open; tCK = tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING | IDD3P | TBD | mA |
| Active standby current; All banks open; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, /CS is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING | IDD3N | TBD | mA |
| Operating burst read current; All banks open, Continuous burst reads, IOU _T = 0mA; BL = 4, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, /CS is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W | IDD4R | TBD | mA |
| Operating burst write current; All banks open, Continuous burst writes; BL = 8, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, /CS is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING IDD4R | IDD4W | TBD | mA |
| Burst refresh current; tCK = tCK(IDD); Refresh command at every tRFC(IDD) interval; CKE is HIGH, /CS is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING | IDD5 | TBD | mA |
| Self refresh current; CK and /CK at 0V; CKE = 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING | IDD6 | TBD | mA |
| Operating bank interleave read current; All bank interleaving reads, IOU _T = 0mA; BL = 8, CL = CL(IDD), AL = tRCD(IDD)-1*tCK(IDD); tCK = tCK(IDD), Trc = tRC(IDD), tRRD = tRRD(IDD), tRCD = 1*tCK(IDD); CKE is HIGH, CS is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data pattern is same as IDD4R; | IDD7 | TBD | mA |

Note: 1. Module IDD was calculated on the specific brand DRAM(2Xnm) component IDD and can be differently measured according to DQ loading capacitor.

Timing Parameters & Specifications

| Speed | | DDR4 2133 | | Unit |
|--|----------|------------------|--------|-------|
| Parameter | Symbol | Min | Max | |
| Average Clock Period | tCK | 0.938 | <1.071 | ns |
| CK high-level width | tCH | 0.48 | 0.52 | tCK |
| CK low-level width | tCL | 0.48 | 0.52 | tCK |
| DQS_t,DQS_c to DQ skew, per group, per access | tDQSQ | - | TBD | tCK/2 |
| DQS_t,DQS_c to DQ Skew deterministic, per group, per access | tDQSQ | - | TBD | tCK/2 |
| DQ output hold time from DQS_t,DQS_c | tQH | TBD | - | tCK/2 |
| DQ output hold time deterministic from DQS_t, DQS_c | tQH | TBD | - | UI |
| DQS_t,DQS_c to DQ Skew total, per group, per access; DBI enabled | tDQSQ | - | TBD | UI |
| DQ output hold time total from DQS_t, DQS_c; DBI enabled | tQH | TBD | - | UI |
| DQ to DQ offset , per group, per access referenced to DQS_t, DQS_c | tDQSQ | TBD | TBD | UI |
| DQS_t, DQS_c differential READ Preamble (2 clock preamble) | tRPRE | 0.9 | TBD | tCK |
| DQS_t, DQS_c differential READ Postamble | tRPST | TBD | TBD | tCK |
| DQS_t, DQS_c differential WRITE Preamble | tWPRE | 0.9 | - | tCK |
| DQS_t, DQS_c differential WRITE Postamble | tWPST | TBD | TBD | tCK |
| DQS_t and DQS_c low-impedance time (Referenced from RL-1) | tLZ(DQS) | -360 | 180 | ps |
| DQS_t and DQS_c high-impedance time (Referenced from RL+BL/2) | tHZ(DQS) | - | 180 | ps |
| DQS_t, DQS_c differential input low pulse width | tDQSL | 0.46 | 0.54 | tCK |
| DQS_t, DQS_c differential input high pulse width | tDQSH | 0.46 | 0.54 | tCK |
| DQS_t, DQS_c rising edge to CK_t, CK_c rising edge (1 clock preamble) | tDQSS | -0.27 | 0.27 | tCK |
| DQS_t, DQS_c falling edge setup time to CK_t, CK_c rising edge | tDSS | 0.18 | - | tCK |
| DQS_t, DQS_c falling edge hold time from CK_t, CK_c rising edge | tDSH | 0.18 | - | tCK |
| Delay from start of internal write transaction to internal read command for different bank group | tWTR_S | Max(2nCK, 2.5ns) | - | |
| Delay from start of internal write transaction to internal read command for same bank group | tWTR_L | Max(4nCK,7.5ns) | - | |
| WRITE recovery time | tWR | 15 | - | ns |
| Mode Register Set command cycle time | tMRD | 8 | - | nCK |

| | | | | |
|---|----------------|------------------|------------|-------------|
| CAS_n to CAS_n command delay for same bank group | tCCD_L | 6 | - | nCK |
| Speed | | DDR4 2133 | | Unit |
| Parameter | Symbol | Min | Max | |
| CAS_n to CAS_n command delay for different bank group | tCCD_S | 4 | - | nCK |
| Auto precharge write recovery + precharge time | tDAL | tWR+tRP/tCK | | nCK |
| ACTIVATE to ACTIVATE Command delay to different bank group for 2KB page size | tRRD_S(2K) | Max(4nCK,5.3ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to different bank group for 1KB page size | tRRD_S(1K) | Max(4nCK,3.7ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to different bank group for 1/ 2KB page size | tRRD_S (1/ 2K) | Max(4nCK,3.7ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to same bank group for 2KB page size | tRRD_L(2K) | Max(4nCK,6.4ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to same bank group for 1KB page size | tRRD_L(1K) | Max(4nCK,5.3ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to same bank group for 1/2KB page size | tRRD_L (1/ 2K) | Max(4nCK,5.3ns) | - | nCK |
| Four activate window for 2KB page size | tFAW_2K | Max(28nCK, 30ns) | - | ns |
| Four activate window for 1KB page size | tFAW_1K | Max(20nCK, 21ns) | - | ns |
| Four activate window for 1/2KB page size | tFAW_1/2K | Max(16nCK, 15ns) | - | ns |
| Power-up and RESET calibration time | tZQinit | 1024 | - | nCK |
| Normal operation Full calibration time | tZQoper | 512 | - | nCK |
| Normal operation short calibration time | tZQCS | 128 | - | nCK |
| Exit Self Refresh to commands not re-quiring a locked DLL | tXS | tRFC(min)+ 10ns | - | |
| Exit Self Refresh to commands requir-ing a locked DLL | tXSDLL | tDLLK(min) | - | |
| Internal READ Command to PRE-CHARGE Command delay | tRTP | Max(4nCK,7.5ns) | - | |
| Minimum CKE low width for Self re-fresh entry to exit timing | tCKESR | tCKE(min)+1nCK | - | |
| Exit Power Down with DLL on to any valid command;Exit Precharge Power Down with DLL frozen to commands not requiring a locked DLL | tXP | Max (4nCK,6ns) | - | |
| CKE minimum pulse width | tCKE | Max (3nCK,5ns) | - | |
| Asynchronous RTT turn-on delay (Power-Down with DLL frozen) | tAONAS | 1.0 | 9.0 | ns |
| Asynchronous RTT turn-off delay (Power-Down with DLL frozen) | tAOFAS | 1.0 | 9.0 | ns |
| RTT dynamic change skew | tADC | 0.3 | 0.7 | tCK |

SERIAL PRESENCE DETECT SPECIFICATION

| AQD-D4U8GN21-SG Serial Presence Detect | | | |
|--|--|---|-------------|
| Byte No. | Function Described | Standard Specification | Vendor Part |
| 0 | Number of Bytes Used / Number of Bytes in SPD Device / CRC Coverage | CRC:0-255Byte SPD Byte use: 512Byte SPD Byte total: 512Byte | 24 |
| 1 | SPD Revision | - | - |
| 2 | Key Byte / DRAM Device Type | DDR4 SDRAM | 0C |
| 3 | Key Byte / Module Type | UDIMM | 02 |
| 4 | SDRAM Density and Banks | 4Gb, 16banks | 84 |
| 5 | SDRAM Addressing | ROW:15, Column:10 | 19 |
| 6 | SDRAM Package Type | - | - |
| 7 | SDRAM Optional Features | - | - |
| 8 | SDRAM Thermal and Refresh Options | - | - |
| 9 | Other SDRAM Optional Features | - | - |
| 10 | Reserved | - | 00 |
| 11 | Module Nominal Voltage, VDD | 1.2V | 03 |
| 12 | Module Organization | 1Rank, 8bits | 09 |
| 13 | Module Memory Bus Width | Non ECC, 64bits | 03 |
| 14 | Module Thermal Sensor | Support | 80 |
| 15-16 | Reserved | - | 00 |
| 17 | Timebases | - | 00 |
| 18 | SDRAM Minimum Cycle Time (tCKAVGmin) | 0.938ns | 08 |
| 19 | SDRAM Maximum Cycle Time (tCKAVGmax) | 1.5ns | 0C |
| 20-23 | CAS Latencies Supported | 10, 11, 12, 13, 14, 15, 16 | - |
| 24 | Minimum CAS Latency Time (tAmin) | 13.5ns | 6C |
| 25 | Minimum RAS to CAS Delay Time (tRCDmin) | 13.5ns | 6C |
| 26 | Minimum Row Precharge Delay Time (tRPmin) | 13.5ns | 6C |
| 27 | Upper Nibbles for tRASmin and tRCmin | - | 11 |
| 28 | Minimum Active to Precharge Delay Time (tRASmin), Least Significant Byte | 33ns | 08 |
| 29 | Minimum Active to Active/Refresh Delay Time (tRCmin), Least Significant Byte | 46.5ns | 74 |
| 30-31 | Minimum Refresh Recovery Delay Time (tRFC1min) | 260ns | 20,08 |
| 32-33 | Minimum Refresh Recovery Delay Time (tRFC2min) | 160ns | 00,05 |
| 34-35 | Minimum Refresh Recovery Delay Time (tRFC4min) | 110ns | 70,03 |
| 36-37 | Minimum Four Activate Window Delay Time (tFAWmin) | 21ns | 00,A8 |
| 38 | Minimum Activate to Activate Delay Time (tRRD_Smin), different bank group | 3.7ns | 1E |
| 39 | Minimum Activate to Activate Delay Time (tRRD_Lmin), same bank group | 5.3ns | 2B |
| 40 | Minimum CAS to CAS Delay Time (tCCD_Lmin), same bank group | 5.355ns | 2B |

| | | | | | | | |
|---------|---|------------------------|----------|----|----|----|----|
| 41-59 | Reserved | - | 00 | | | | |
| 60-77 | Connector to SDRAM Bit Mapping | - | - | | | | |
| 78-116 | Reserved | - | 00 | | | | |
| 117 | Fine Offset for Minimum CAS to CAS Delay Time (tCCD_Lmin), same bank group | - | ED | | | | |
| 118 | Fine Offset for Minimum Activate to Activate Delay Time (tRRD_Lmin), same bank group | - | B5 | | | | |
| 119 | Fine Offset for Minimum Activate to Activate Delay Time (tRRD_Smin), different bank group | - | CE | | | | |
| 120 | Fine Offset for Minimum Active to Active/Refresh Delay Time (tRCmin) | - | 00 | | | | |
| 121 | Fine Offset for Minimum Row Precharge Delay Time (tRPmin) | - | 00 | | | | |
| 122 | Fine Offset for Minimum RAS to CAS Delay Time (tRCDmin) | - | 00 | | | | |
| 123 | Fine Offset for Minimum CAS Latency Time (tAamin) | - | 00 | | | | |
| 124 | Fine Offset for SDRAM Maximum Cycle Time (tCKAVGmax) | - | 00 | | | | |
| 125 | Fine Offset for SDRAM Minimum Cycle Time (tCKAVGmin) | - | C2 | | | | |
| 126-127 | Cyclical Redundancy Code | - | - | | | | |
| 128 | Raw Card Extension, Module Nominal Height | 32mm | 11 | | | | |
| 129 | Module Maximum Thickness | Planar Double Sides | 11 | | | | |
| 130 | Reference Raw Card Used | Revision 0, Raw card B | 01 | | | | |
| 131 | Address Mapping from Edge Connector to DRAM | Mirrored | 01 | | | | |
| 132-253 | Reserved | - | 00 | | | | |
| 254-255 | Cyclical Redundancy Code (CRC) | - | - | | | | |
| 256-319 | Reserved | - | 00 | | | | |
| 320-321 | Module Manufacturer ID Code | Transcend | 01,4F | | | | |
| 322 | Module Manufacturing Location | Taipei | 54 | | | | |
| 323-324 | Module Manufacturing Date | - | 00 | | | | |
| 325-328 | Module Serial Number | - | 00 | | | | |
| 329-348 | Module Part Number | AQD-D4U8GN21-SG | 41 | 51 | 44 | 2D | 44 |
| | | | 34 | 55 | 38 | 47 | 4E |
| | | | 32 | 31 | 2D | 53 | 47 |
| | | | 20 | 20 | 20 | 20 | 20 |
| 349 | Module Revision Code | - | 00 | | | | |
| 350-351 | DRAM Manufacturer ID Code | By Manufacturer | Variable | | | | |
| 352 | DRAM Stepping | - | 00 | | | | |
| 353-381 | Manufacturer Specific Data | By Manufacturer | Variable | | | | |
| 382-383 | Reserved | - | 00 | | | | |
| 384-551 | End User Programmable | - | - | | | | |



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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